NSN 5961-01-043-6253

Photo Semiconductor Device - Page 1 of 1



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Inclosure Material:
Ceramic and metal and glass
Overall Length:
Between 0.102 inches and 0.115 inches
Overall Diameter:
Between 0.058 inches and 0.061 inches
Function For Which Designed:
Phototransistor
Internal Configuration:
Junction contact
Mounting Method:
Press fit
Features Provided:
Gold plated leads and hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
50.0 collector to emitter voltage, dc and 7.0 emitter to collector voltage, dc
Current Rating Per Characteristic:
0.50 milliamperes collector cutoff current, dc, emitter open and 3.00 milliamperes peak forward surge current
Power Rating Per Characteristic:
50.0 milliwatts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: npn
Precious Material And Location:
Ocase and terminal surfaces gold
Terminal Type And Quantity:
1 case and 2 tab, solder lug
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:
A110a0